RF2127 RF POWER BIPOLAR TRANSISTORS VHF MOBILE APPLICATIONS

FEATURES SUMMARY

- ∎175 MHz
- ∎12.5 VOLTS
- ■COMMON EMITTER
- ■POUT = 100 W MIN. WITH 6.0 dB GAIN

DESCRIPTION

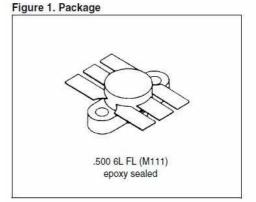


Figure 2. Pin Connection

The RF2127 is a 12.5 V Class C epitaxial silicon NPN planar transistor designed primarily for VHF FM communications. This device utilizes diffused emitter resistors to withstand extremely high VSWR under rated operating conditions, and is internally input matched to optimize power gain and efficiency over the 136 - 175 MHz band.

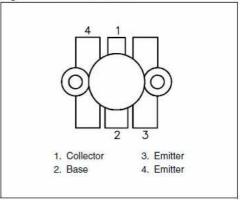


Table 1. Order Codes

| Order Codes | Marking | Package | Packaging |
|-------------|---------|---------|---------------|
| RF2127 | RF2127 | M111 | PLASTIC TRAYS |

| Symbo | Parameter | Value | Unit | |
|----------------------|----------------------------------|--------------|------|--|
| Vcbo | Collector-Base Voltage | 36 | V | |
| VCEO | Collector-Emitter Voltage | 18 | V | |
| VCES | Collector-Emitter Voltage | 36 | V | |
| VEBO | Emitter-Base Voltage | 4.0 | V | |
| c | Device Current | 20 | А | |
| PDISS | Power Dissipation | 270 | w | |
| TJ | Junction Temperature | +200 | °C | |
| TSTG | Storage Temperature | - 65 to +150 | °C | |
| IERMAL DA | ATA | | | |
| R _{TH(j-c)} | Junction-Case Thermal Resistance | 0.65 | °C/W | |

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

| ELECTRICAL SPECIFICATIONS (Te | case = 25°C) |
|-------------------------------|--------------|
|-------------------------------|--------------|

STATIC

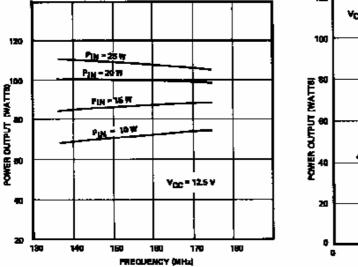
| Symbol | Test Conditions | Value | | | Unit |
|--------|---|-------|------|------|------|
| | Test Conditions | | Тур. | Max. | onit |
| ВVсво | $I_{\rm C} = 50 \text{mA}$ $I_{\rm E} = 0 \text{mA}$ | 36 | — | — | V |
| BVCES | $I_C = 100 \text{mA}$ $V_{BE} = 0 \text{V}$ | 36 | — | _ | V |
| BVCEO | $I_{\rm C} = 100 \text{mA}$ $I_{\rm B} = 0 \text{mA}$ | 18 | — | | V |
| BVEBO | $I_E = 10 \text{mA}$ $I_C = 0 \text{mA}$ | 4.0 | — | _ | V |
| CES | $V_{CE} = 15V$ $I_E = 0mA$ | | | 15 | mA |
| hFE | $V_{CE} = 5V$ $I_C = 5A$ | 10 | _ | _ | _ |

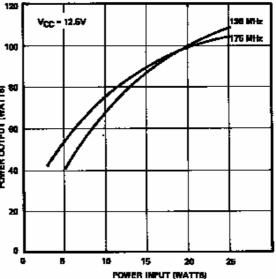
DYNAMIC

| Symbol | Test Conditions | | | Value | | | |
|--------|------------------------|-------------------------|-------------------|-------|------|------|------|
| Symbol | Symbol Test conditions | | | Min. | Тур. | Max. | Unit |
| Pout | f = 175 MHz | $P_{IN} = 25 \text{ W}$ | $V_{CC} = 12.5 V$ | 100 | — | | w |
| GP | f = 175 MHz | $P_{IN} = 25 W$ | Vcc = 12.5 V | 6.0 | — | | dB |
| Сов | f = 1 MHz | $V_{CB}=12.5\ V$ | | | 350 | | pF |

POWER OUTPUT vs FREQUENCY

POWER OUTPUT vs POWER INPUT





MPEDANCE DATA

